

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C
-30V	77mΩ @ V _{GS} = -10V	-3.5A
	95mΩ @ V _{GS} = -4.5V	-3.0A
	150mΩ @ V _{GS} = -2.5V	-2.4A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

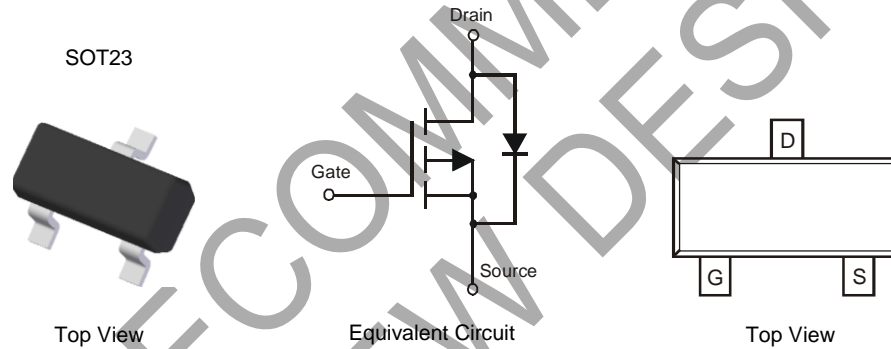
- DC-DC Converters
- Power Management Functions
- Analog Switch

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMP3130LQ](#))**

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 [Ⓜ]
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

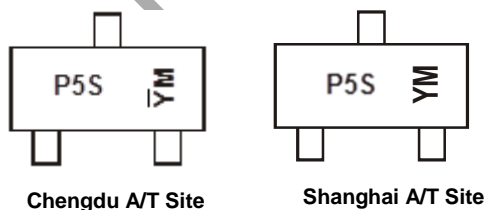


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3130L-7	SOT23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



P5S = Product Type Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test Site)
 ȲM = Date Code Marking for CAT (Chengdu Assembly/ Test Site)
 Y or Ȳ = Year (ex: E = 2017)
 M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018	
Code	V	W	X	Y	Z	A	B	C	D	E	F	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-30	V	
Gate-Source Voltage	V _{GSS}	±12	V	
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	-3.0 -2.6	A
	t < 10s	T _A = +25°C T _A = +70°C	-4.1 -3.2	A
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	-1.6	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-20	A	

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P _D	T _A = +25°C	0.7	W
		T _A = +70°C	0.4	
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady State	184	°C/W
		t < 10s	115	
Total Power Dissipation (Note 6)	P _D	T _A = +25°C	1.3	W
		T _A = +70°C	0.8	
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady State	94	°C/W
		t < 10s	61	
Thermal Resistance, Junction to Case	R _{θJC}	25		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -30V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.6	—	-1.3	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	59	77	mΩ	V _{GS} = -10V, I _D = -4.2A
		—	73	95		V _{GS} = -4.5V, I _D = -4A
		—	115	150		V _{GS} = -2.5V, I _D = -3A
Forward Transconductance	g _{fs}	—	8	—	S	V _{DS} = -5V, I _D = -4A
Source-Drain Diode Forward Voltage	V _{SD}	—	-0.8	-1.25	V	V _{GS} = 0V, I _S = -3.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	432	864	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	87	174	pF	
Reverse Transfer Capacitance	C _{rss}	—	62	124	pF	
Gate Resistance	R _G	—	4.04	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q _G	—	5.9	11.8	nC	V _{DS} = -15V, V _{GS} = -4.5V, I _D = -4.0A
		—	12	24		V _{DS} = -15V, V _{GS} = -10V, I _D = -4.0A
Gate-Source Charge	Q _{GS}	—	1.0	2.0	ns	V _{DS} = -15V, V _{GS} = -4.5V, I _D = -4.0A
Gate-Drain Charge	Q _{GD}	—	3.1	6.2		
Turn-On Delay Time	t _{D(ON)}	—	4.6	9.2	ns	V _{DS} = -15V, V _{GS} = -10V, I _D = -1A, R _G = 6.0Ω
Rise Time	t _r	—	6.5	13.0		
Turn-Off Delay Time	t _{D(OFF)}	—	27.8	55.6		
Fall Time	t _f	—	15.0	30.0		

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

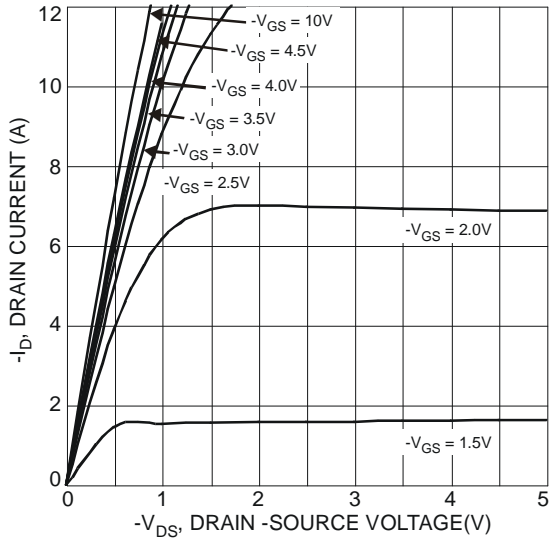


Fig. 1 Typical Output Characteristics

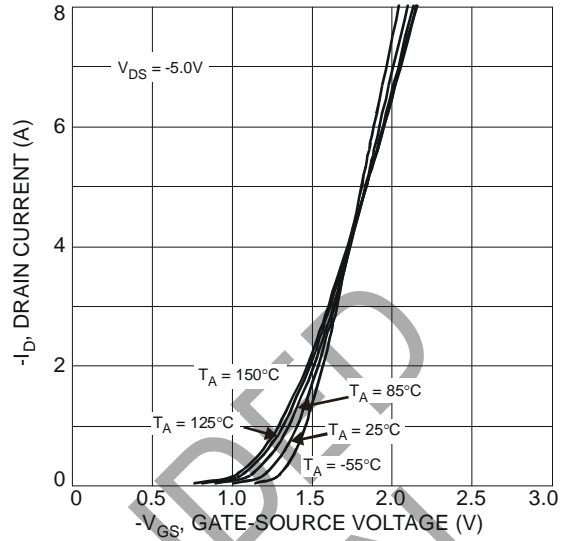


Fig. 2 Typical Transfer Characteristics

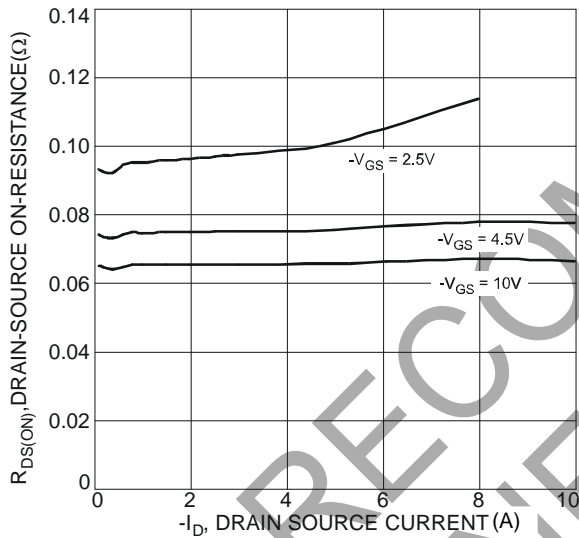


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

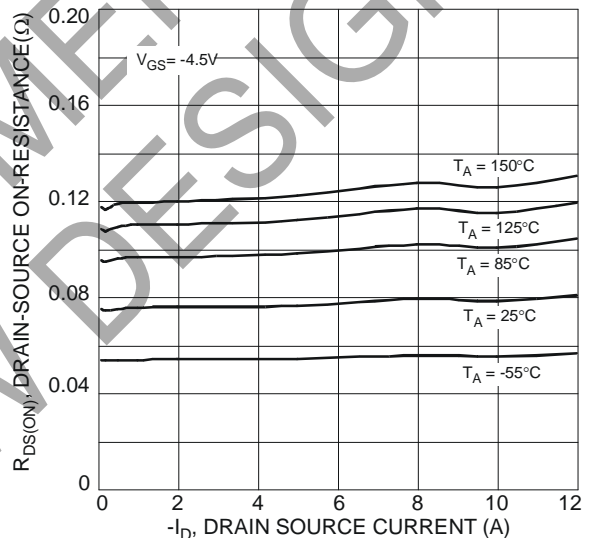


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

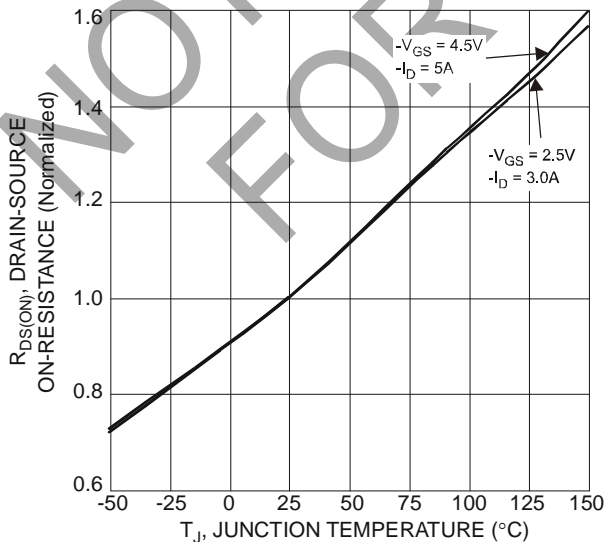


Fig. 5 On-Resistance Variation with Temperature

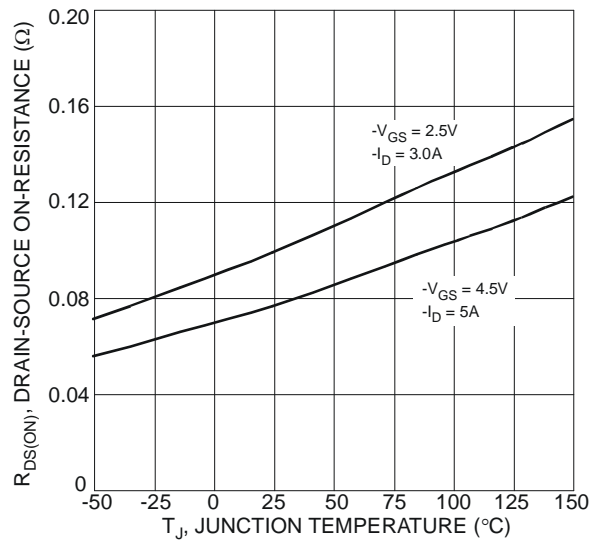


Fig. 6 On-Resistance Variation with Temperature

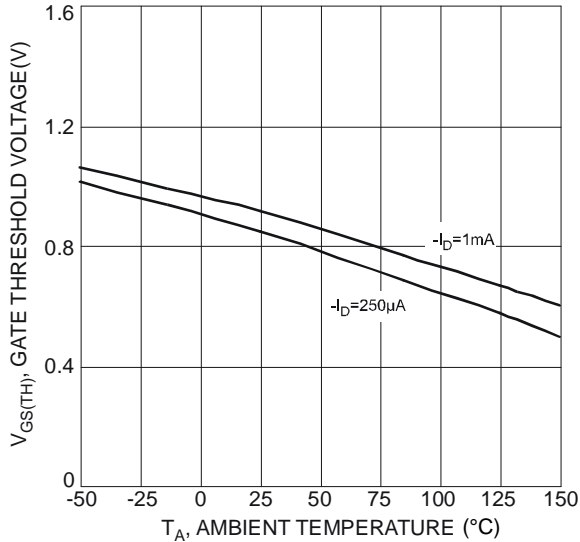


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

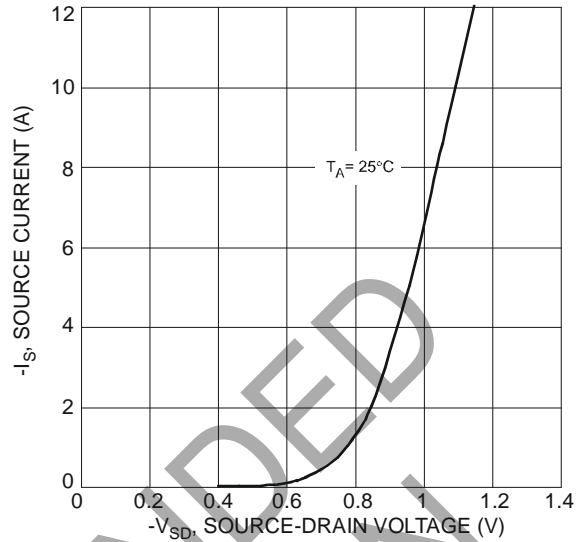


Fig. 8 Diode Forward Voltage vs. Current

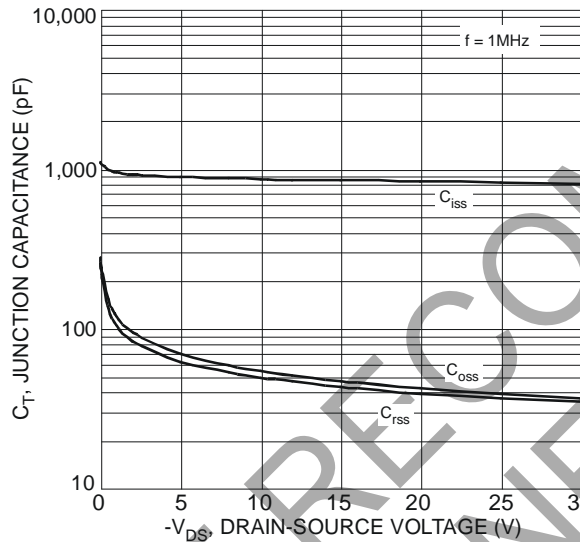


Fig. 9 Typical Junction Capacitance

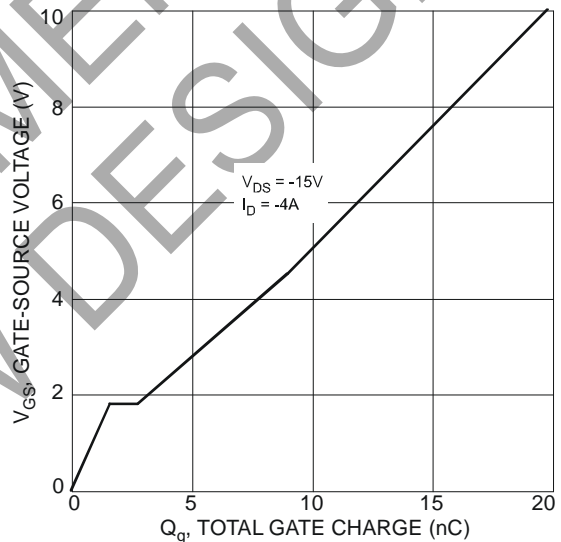


Fig. 10 Gate-Charge Characteristics

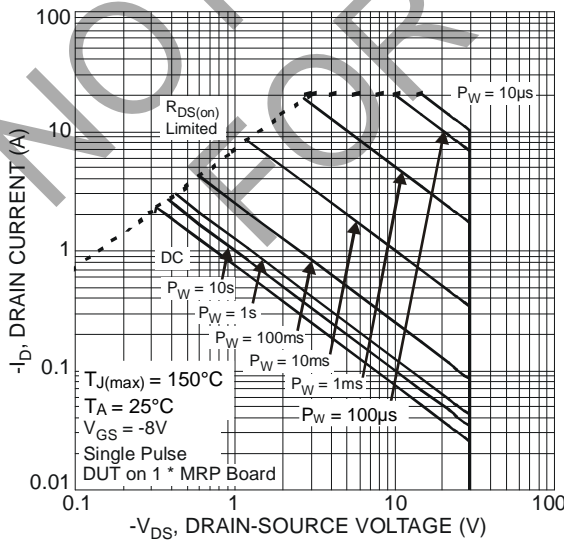
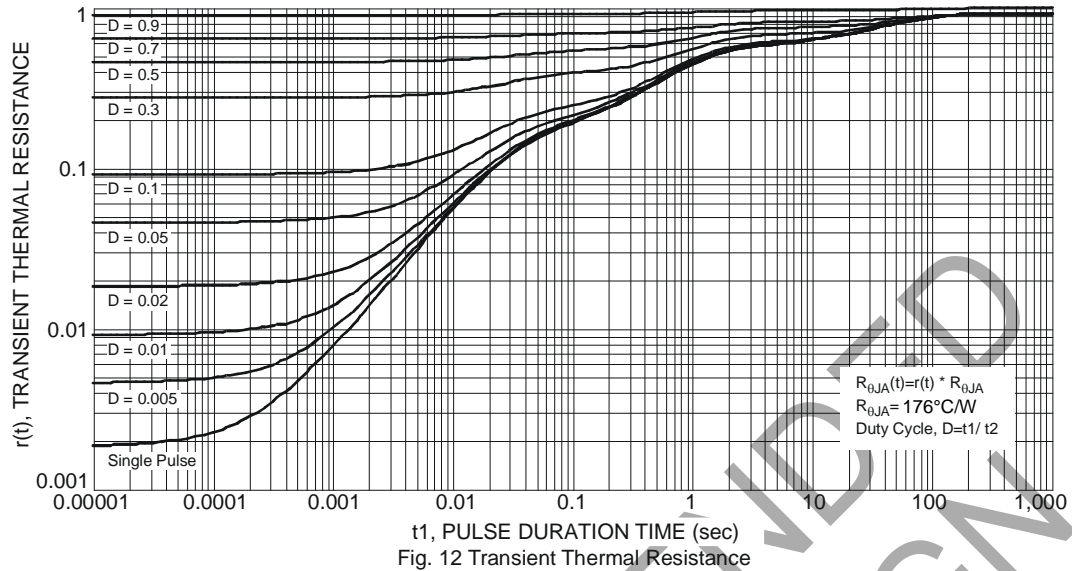


Fig. 11 SOA, Safe Operation Area

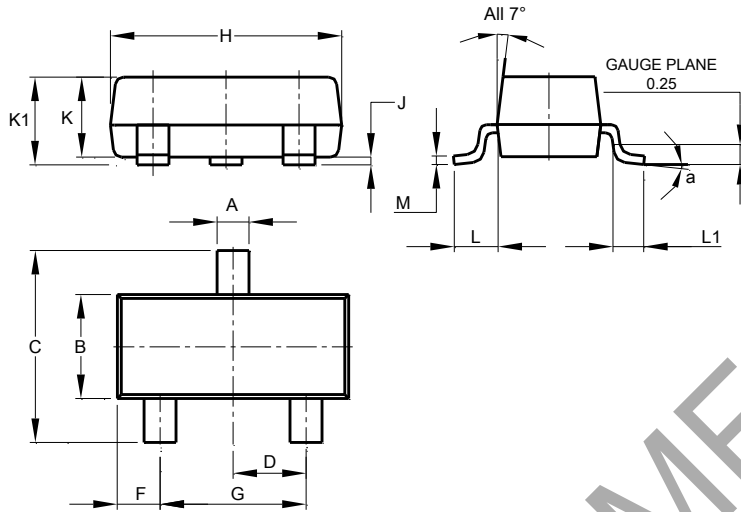


NOT RECOMMENDED FOR NEW DESIGN

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

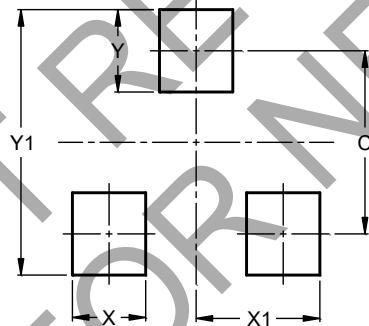


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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